

Contents of Applied Physics A 54

This listing presents the papers in alphabetical order of the first author, subdivided into the sections "Solids and Materials: Physical and Chemical Properties" and "Surfaces and Multilayers: Growth, Modification, and Integration". The Author Index that follows covers **Applied Physics A** and **B**, and is presented in tabular form. The names are listed in alphabetical order in the first column. The second and third columns contain the bibliographic data necessary to locate the paper. The issue is specified by the number separated from the volume number by a slash. The PACS numbers given in the fourth column may be used in conjunction with the PACS listing on the left to infer the topic of a paper.

Solids and Materials

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Scattering study of vitrifying Cr-Ti solutions.
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Flashlamp-pumped Ti:sapphire laser with different rods grown by Czochralski and Verneuil methods.
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Experimental study of positron motion in kapton.
Appl. Phys. A 54/3, 233-238 (1992) PACS: 66.30 71.60 78.70
- Cruz R.M. de la, Pareja R., Segura A., Moser P., Chevy A.:
Positrons and electron-irradiation induced defects in the layered semiconductor InSe.
Appl. Phys. A 54/2, 147-151 (1992) PACS: 78.70B 61.80 72.80
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Mechanism of ion-beam-enhanced diffusion in amorphous silicon.
Appl. Phys. A 54/6, 481-484 (1992) PACS: 72.80 61.80 66.30
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- Fagotto E.A.M., Costa C.H.C.R., Decker F., Fracastoro-Decker M.:
Thermal wave electroacoustic calorimetry in a Si photovoltaic cell.
Appl. Phys. A 54/1, 1-5 (1992) PACS: 72.50 78.20
- Foerster C.E., Amaral L., Moncoffre N., Behar M.:
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An optical bridge reflectometer for sensitive measurement of ion implantation dose.
Appl. Phys. A 54/6, 570-572 (1992) PACS: 06.70D 42.80 89.20
- Hohenstein M.:
Single sideband imaging in high-resolution electron microscopy.
Appl. Phys. A 54/6, 485-492 (1992) PACS: 07.80 61.60
- Hunt A.:
A method for distinguishing power-law and approximate power-law behavior in glassy relaxation: Ionic conducting glasses.
Appl. Phys. A 54/6, 508-510 (1992) PACS: 66.10 66.30
- Ivanov-Shitz A.K., Buchstab A.S., Aityan S.K., Kohler H.-H.:
Molecular dynamics simulation of the superionic conductor BaF₂.
Appl. Phys. A 54/3, 251-257 (1992) PACS: 63.00 64.00 66.30
- Jauregui J., Matthias E.:
Thermal diffusivities measured by photodisplacement detection of transient thermal gratings.
Appl. Phys. A 54/1, 35-39 (1992) PACS: 44.50 65.70
- JIN Hua, HU Zhuangqi, LIU Qingmin, GE Yunlong, SHI Changxu:
Crystallization process of Bi(Pb)-Sr-Ca-Cu-O glass.
Appl. Phys. A 54/5, 399-403 (1992) PACS: 74.70 81.20 81.40
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On the possibility of wake-field effects in the conductivity of doped semiconductors.
Appl. Phys. A 54/2, 132-138 (1992) PACS: 72.20H 71.45
- Lau F.:
Modeling of polysilicon diffusion sources during rapid optical annealing.
Appl. Phys. A 54/2, 139-146 (1992) PACS: 66.30J 64.75
- Lewis W.B.:
Single crystal EPR spectrum of Cr³⁺ in lanthanum lutecium gallium garnet.
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Description of non-equilibrium phenomena in pulsed MOS capacitors.
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Optimized procedure for the manufacture of thin film filter prototypes.
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Optically controlled characteristics of a new heterojunction field effect transistor.
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